

IN THE CLAIMS:

Please cancel claims 1-15 without prejudice or disclaimer, and add new claims 25-30 as follows:

1-24. (Cancelled)

25. (New) A semiconductor device comprising:

a semiconductor chip including a MISFET;

a source electrode of the MISFET formed on a bottom surface of the semiconductor chip;

a gate electrode of the MISFET formed on a bottom surface of the semiconductor chip;

a drain electrode formed on a top surface of the semiconductor chip;

a drain electrode terminal positioned over the drain electrode and electrically connected with the drain electrode, the drain electrode terminal extending from over the top surface of the semiconductor chip to under the bottom surface of the semiconductor chip;

a source electrode terminal positioned under the source electrode and electrically connected with the source electrode;

a gate electrode terminal positioned under the source electrode and electrically connected with the gate electrode; and

a sealing member sealing the semiconductor chip and parts of the drain, source and gate electrode terminals,


wherein the source and gate electrode terminals are exposed from a bottom surface of the sealing member,

the drain electrode terminal are exposed from a top surface and the bottom surface to the sealing member,

the sealing member has a first side face, a second side face, a third side face and a fourth side face,

the first and second side faces are opposite each other, and the third and fourth side faces are opposite each other,

the first side surface of the sealing member connects to the third and fourth side faces of the sealing member, and the second side surface of the sealing member connects to the third and fourth side faces of the sealing member,



the source and gate electrode terminals are exposed from the first and second side faces of the sealing member, and

the drain electrode terminal is exposed from the third and fourth side faces of the sealing member.

26. (New) A semiconductor device according to Claim 25, wherein the drain electrode terminal is disposed perpendicular to the source and gate electrode terminals in a plan view.
27. (New) A semiconductor device according to Claim 25, wherein a source bump electrode is formed on the source electrode, and electrically connected with the source electrode; and
a gate bump electrode is formed on the gate electrode, and electrically connected with the gate electrode.
28. (New) A semiconductor device according to Claim 27, wherein the source and gate bump electrodes are connected with the source and gate electrode terminals respectively through adhesives.
29. (New) A semiconductor device according to Claim 25, wherein the drain, source and gate electrode terminals are made of lead frames.
30. (New) A semiconductor device according to Claim 25, wherein the sealing member is comprised of an insulating resin.